

CLAIM AMENDMENTS

Please replace the pending claims with the following listing of claims:

1-49. (Canceled).

50. (Currently Amended) A nitride semiconductor structure comprising on a substrate:

an n-type collector layer;

a p-type base layer which is at least one of layers formed on said n-type collector layer; and

an n-type emitter layer formed on said p-type base layer, wherein

a surface of said p-type base layer, which is exposed by etching said n-type emitter layer, is provided with an indium-containing p-type nitride semiconductor layer, which is regrown on said surface.

51. (Original) The nitride semiconductor structure according to claim 50, wherein said p-type nitride semiconductor layer is p-type InGaN.

52. (Original) The nitride semiconductor structure according to claim 51, wherein said p-type base layer is p-type InGaN.

53. (Original) The nitride semiconductor structure according to claim 51, wherein said p-type InGaN base layer has an indium mole fraction of 5 - 30%.

54. (Original) The nitride semiconductor structure according to claim 51, wherein said p-type nitride semiconductor layer has an indium mole fraction higher than an indium mole fraction of said p-type InGaN base layer.

55. (Original) The nitride semiconductor structure according to claim 50, wherein said p-type base layer is p-type InGaN.

56. (Original) The nitride semiconductor structure according to claim 55, wherein said p-type InGaN base layer has an indium mole fraction of 5 - 30%.

57. (Original) The nitride semiconductor structure according to claim 55, wherein said p-type nitride semiconductor layer has an indium mole fraction higher than an indium mole fraction of said p-type InGaN base layer.

58. (Original) The nitride semiconductor structure according to claim 50, wherein said p-type InGaN base layer has an indium mole fraction of 5 - 30%.

59. (Original) The nitride semiconductor structure according to claim 58, wherein said p-type nitride semiconductor layer has an indium mole fraction higher than an indium mole fraction of said p-type InGaN base layer.

60. (Original) The nitride semiconductor structure according to claim 50, wherein said p-type nitride semiconductor layer has an indium mole fraction higher than an indium mole fraction of said p-type InGaN base layer.

61.-76. (Cancelled)

77. (New) The nitride semiconductor structure according to claim 50, further comprising a graded layer between said p-type base layer and said n-type collector layer, said graded layer has its indium mole fraction varied gradually.

78. (New) The nitride semiconductor structure according to claim 51, further comprising a graded layer between said p-type base layer and said n-type collector layer, said graded layer has its indium mole fraction varied gradually.

79. (New) The nitride semiconductor structure according to claim 55, further comprising a graded layer between said p-type base layer and said n-type collector layer, said graded layer has its indium mole fraction varied gradually.